# P-Channel 60 V (D-S) MOSFET

DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC
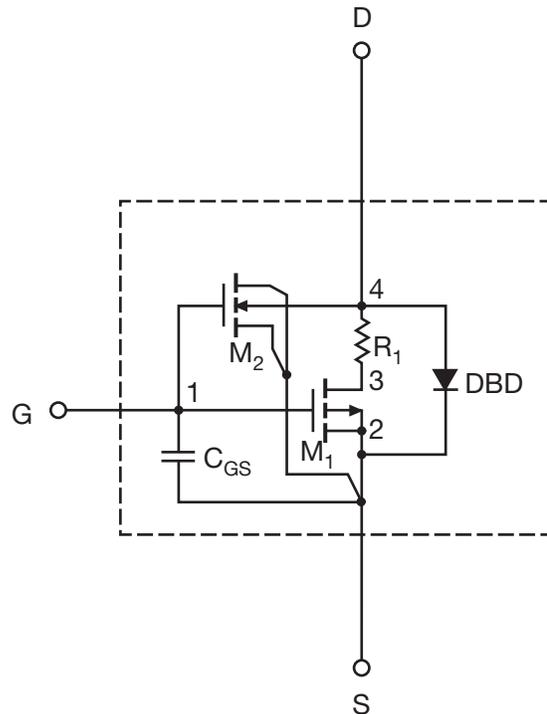
Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = - 250 µA	2.1	-	V
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = - 5 V, V_{GS} = - 10 V	88	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 5.7 A	0.053	0.054	Ω
		V_{GS} = - 4.5 V, I_D = - 4.4 A	0.084	0.090	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 5.7 A	11	11	S
Diode Forward Voltage	V_{SD}	I_S = - 3.2 A, V_{DS} = 0 V	- 0.82	- 0.80	V
Dynamic[b]					
Total Gate Charge	Q_g	V_{DS} = - 30 V, V_{GS} = - 10 V, I_D = - 5.7 A	15.4	15	nC
Gate-Source Charge	Q_{gs}		4	4	
Gate-Drain Charge	Q_{gd}		3.2	3.2	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 30 V, R_L = 30 Ω I_D = - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω	9	12	ns
Rise Time	t_r		12	12	
Turn-Off Delay Time	$t_{d(off)}$		19	22	
Fall Time	t_f		32	16	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = - 3.2 A, dI/dt = 100 A/µs	31	45	

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)
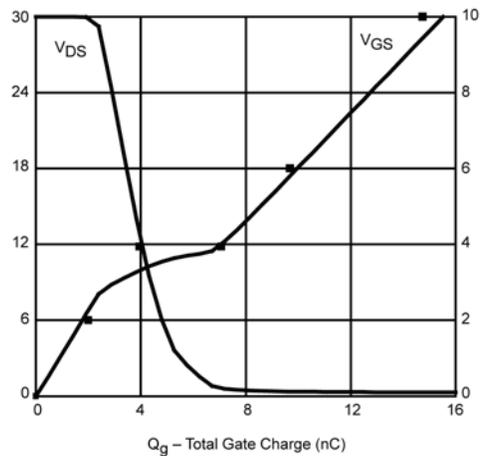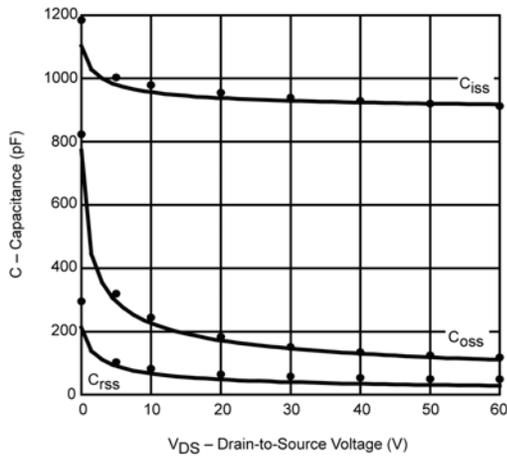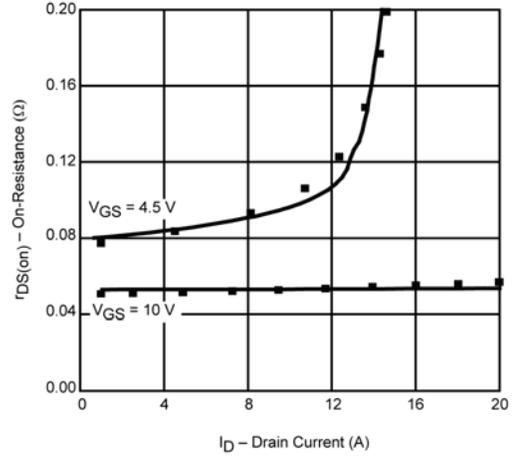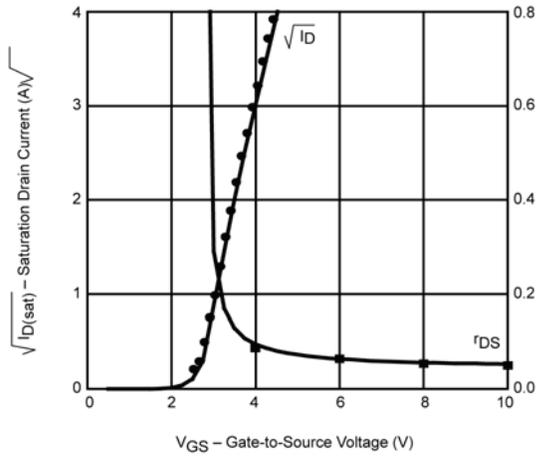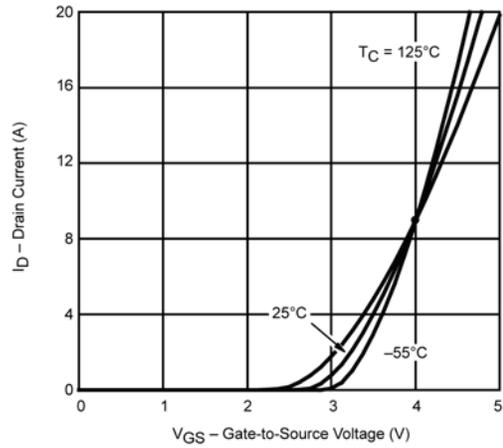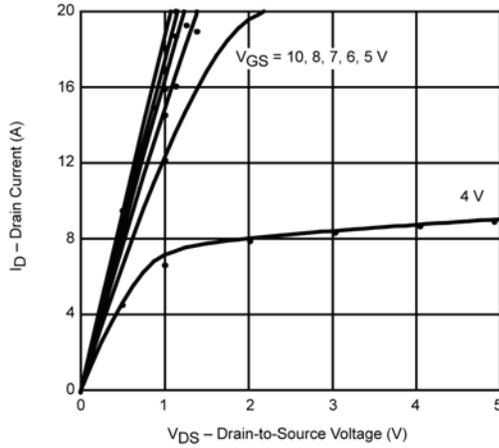
Note
• Dots and squares represent measured data.